1. Title:	The study for Image placement accuracy of EUV mask on the flat chuck
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3. Abstract body:
EUV lithography is a strong candidate to be applied for 32-nm or beyond.
NuFlare has been proposing to use offline blank backside topography correction, OBBTC, for EUV mask writing to compensate blank deformation when the mask is held on the electrostatic chuck. We are expecting to be able to relax the specification for EUV blank with OBBTC.
Chucking repeatability in the scanner or metrology tool for pattern placement accuracy is necessary to utilize this correction method.
In addtion to the blank backside topography, OBBTC can also compensate the blank deformation by chucking when the mask is held on the scanner or metrology tool if it is repeatable.

We will report that the flatness of blank backside has an impact to chucking repeatability, and show update of pattern grid deformation by chucking with new series of test mask and new vacuum chuck for IPRO2.